

HUIZHOU JINSANE ELECTRONICS CO., LTD

RS1AF THRU RS1MF

FEATURES

- For surface mounted applications
- Low profile package
- Glass Passivated Chip Junction
- Easy to pick and place
- Fast reverse recovery time
- Lead free in comply with EU RoHS 2011/65/EU directives

MECHANICAL DATA

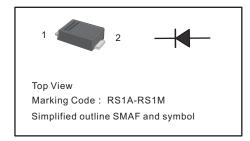
· Case: SMAF

• Terminals: Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 27mg / 0.00095oz

PINNING

PIN	DESCRIPTION				
1	Cathode				
2	Anode				



Absolute Maximum Ratings and Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Parameter	Symbols	RS1AF	RS1BF	RS1DF	RS1GF	RS1JF	RS1KF	RS1MF	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	٧
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V _{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at T_c = 125 °C	I _{F(AV)}	1							А
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load	I _{FSM}	30							А
Maximum Forward Voltage at 1 A	V _F	1.3							V
Maximum DC Reverse Current $T_a = 25 ^{\circ}\text{C}$ at Rated DC Blocking Voltage $T_a = 125 ^{\circ}\text{C}$	I _R	5 50							μA
Typical Junction Capacitance at V_R =4 V , f=1 MHz	C _j	15							pF
Maximum Reverse Recovery Time (1)	t _{rr}	150			250	500		ns	
Typical Thermal Resistance (2)	R _{θJA}	80							°C/W
Operating and Storage Temperature Range	T_{j}, T_{stg}	-55 ~ + 150							°C

^(1) Measured with I_{F} = 0.5 A, I_{R} = 1 A, I_{rr} = 0.25 A.

⁽ 2) P.C.B. mounted with 2.0" X 2.0" (5 X 5 cm) copper pad areas.

Fig.1 Forward Current Derating Curve

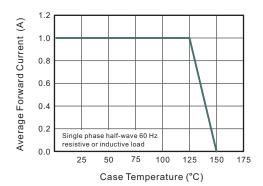


Fig.2 Typical Reverse Characteristics

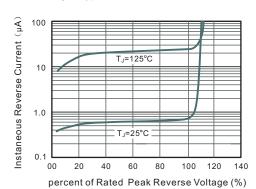


Fig.3 Typical Instaneous Forward Characteristics

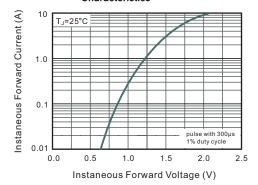


Fig.4 Typical Junction Capacitance

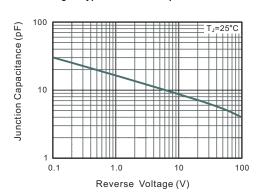


Fig.5 Maximum Non-Repetitive Peak Forward Surage Current

